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|--|---|---|---------------------------|
| | Application No. | Applicant(s) | 7 |
| Al- 4' F All L'124 | 10/540,720 | KISHIMA ET AL. | |
| Notice of Allowability | Examiner | Art Unit | |
| | David Nhu | 2818 | |
| The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313 | (OR REMAINS) CLOSED in this app or other appropriate communication GHTS. This application is subject to | olication. If not includ will be mailed in due | ed course. THIS |
| 1. This communication is responsive to <u>12/14/07</u> . | | | |
| 2. The allowed claim(s) is/are 1,4-7 and 11-17. | | | |
| 3. Acknowledgment is made of a claim for foreign priority uner a) All b) Some* c) None of the: 1. Certified copies of the priority documents have | | | |
| Certified copies of the priority documents have | been received in Application No | | |
| 3. Copies of the certified copies of the priority doc | cuments have been received in this i | national stage applica | tion from the |
| International Bureau (PCT Rule 17.2(a)). | | • | |
| * Certified copies not received: | | | |
| Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. | | | |
| 4. A SUBSTITUTE OATH OR DECLARATION must be subminformal PATENT APPLICATION (PTO-152) which give | | | IOTICE OF |
| 5. CORRECTED DRAWINGS (as "replacement sheets") mus | t be submitted. | | |
| (a) ☐ including changes required by the Notice of Draftspers | on's Patent Drawing Review (PTO- | 948) attached | |
| 1) hereto or 2) to Paper No./Mail Date | | | |
| (b) ☐ including changes required by the attached Examiner's Paper No./Mail Date | s Amendment / Comment or in the O | office action of | |
| Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d). | | | |
| 6. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL. | | | |
| | | | |
| Attachment(s) 1. Notice of References Cited (PTO-892) | 5. ☐ Notice of Informal P | atent Application | |
| 2. Notice of Draftperson's Patent Drawing Review (PTO-948) | 6. Interview Summary | (PTO-413), | |
| 3. Information Disclosure Statements (PTO/SB/08), | Paper No./Mail Dat 7. ☐ Examiner's Amendn | | |
| Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit | 8. 🛛 Examiner's Stateme | ent of Reasons for Allo | owance |
| of Biological Material | 9. | | |
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10/540,720 Art Unit: 2818

EASONS FOR ALLOWANCE

- 1. Claims 1, 4-7, 11-17 are allowed.
- 2. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1, 11: forming a silicon dioxide layer in the single crystal silicon substrate by heat treatment; and removing the mask and the surface protection layer from the single silicon substrate, wherein the silicon dioxide layer has a pattern corresponding to presence/absence and thickness of the mask formed on the major surface of the single-crystal silicon substrate, the pattern having a relatively short distance from the major surface in an area when the mask has been formed and a relatively long distance from the major surface in an area where the mask has not been formed (as cited in claim 1); forming a silicon dioxide layer in the single-crystal silicon substrate by heat treatment; removing the mask and the surface protection layer; and polishing the major surface by a predetermined quality; wherein the silicon dioxide layer has a pattern such that its distance from the major surface in an area where the mask has been formed on the major surface is relatively short while its distance from the major surface in an area where the mask has not been formed is relatively long, and the quantity of polishing is equal to the quantity of removal of the silicon dioxide layer formed in area where the mask has been formed (as cited in claim 11).
- 3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

10/540,720 Art Unit: 2818

- 4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Yamazaki et al (6,803,264 B2): Method of Fabricating a Semiconductor Device.
- 5. Any inquiry concerning this communication on earlier communications from the examiner should be directed to David Nhu, (703) 306-5796.

The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The fax phone number for the organization where this application or proceeding is assigned is (571)273-8300.

David Nhu

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December 28, 2207

DAVID NHUPRIMARY EXAMINER

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